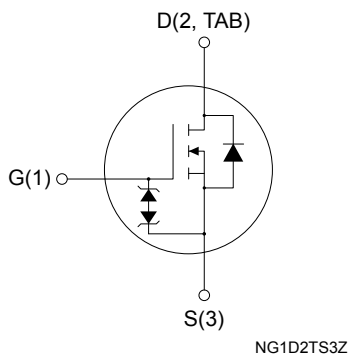
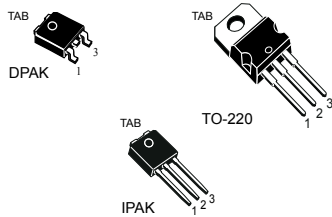


N-channel 650 V, 0.60 Ω typ., 7 A MDmesh™ M2 Power MOSFET in DPAK, TO-220 and IPAK packages



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}	Package
STD11N65M2	650 V	0.68 Ω	7 A	85 W	DPAK
STP11N65M2					TO-220
STU11N65M2					IPAK

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the MDmesh M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.



Product status link

[STD11N65M2](#)
[STP11N65M2](#)
[STU11N65M2](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	7	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	4.4	
$I_{DM}^{(1)}$	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	85	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by T_{jmax} .
2. $I_{SD} \leq 7\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS} (\text{peak}) \leq V_{(BR)DSS}$, $V_{DS} = 400\text{ V}$
3. $V_{DS} \leq 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case	1.47			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	100	
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50			

1. When mounted on a 1-inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	1.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ

1. Pulse width limited by T_{jmax} .
2. starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 650\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 650\text{ V}$, $T_{\text{case}} = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 10	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 3.5\text{ A}$		0.60	0.68	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iSS}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	410	-	pF
C_{oSS}	Output capacitance		-	20	-	
C_{rSS}	Reverse transfer capacitance		-	0.9	-	
$C_{\text{oSS eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0$ to 520 V , $V_{\text{GS}} = 0\text{ V}$	-	43	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	6.4	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 520\text{ V}$, $I_{\text{D}} = 7\text{ A}$, $V_{\text{GS}} = 0$ to 10 V (see Figure 16)	-	12.5	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	
Q_{gd}	Gate-drain charge		-	5.8	-	

1. $C_{\text{oSS eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oSS} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 325\text{ V}$, $I_{\text{D}} = 3.5\text{ A}$, $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 15 and Figure 20)	-	9.5	-	ns
t_{r}	Rise time		-	7.5	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	26	-	
t_{f}	Fall time		-	15	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		28	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 7\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 17)	-	318		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current		-	15.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	437		ns
Q_{rr}	Reverse recovery charge		-	3.2		μC
I_{RRM}	Reverse recovery current		-	15		A

1. Pulse width is limited by safe operating area.

2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

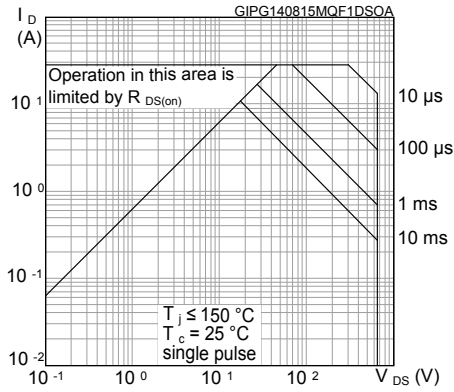
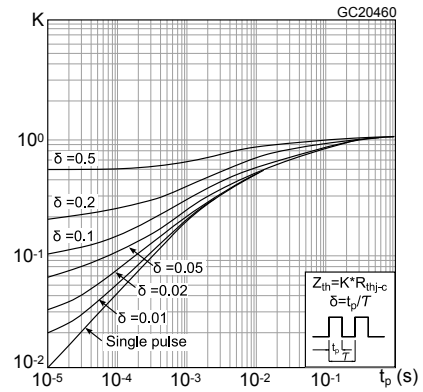
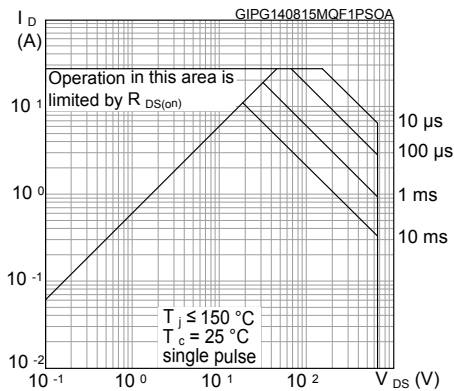
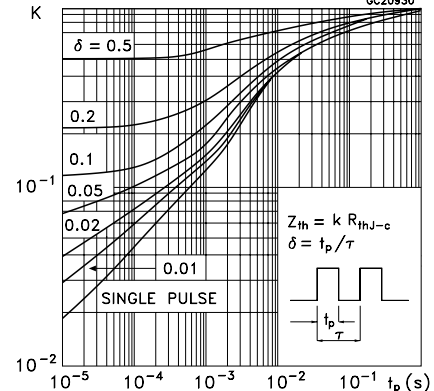
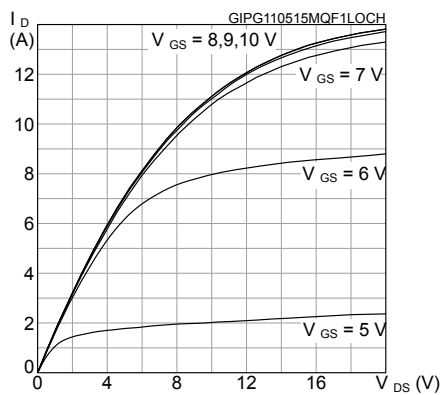
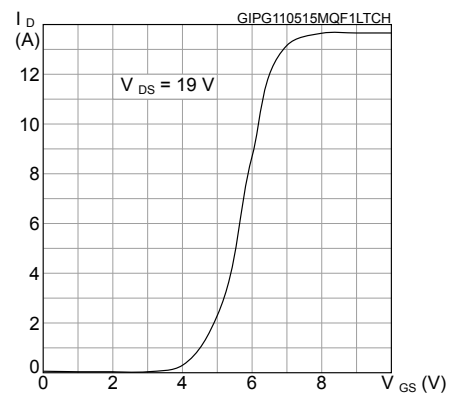
2.1 Electrical characteristics (curves)
Figure 1. Safe operating area for DPAK and IPAK

Figure 2. Thermal impedance for DPAK and IPAK

Figure 3. Safe operating area for TO-220

Figure 4. Thermal impedance for TO-220

Figure 5. Output characteristics

Figure 6. Transfer characteristics


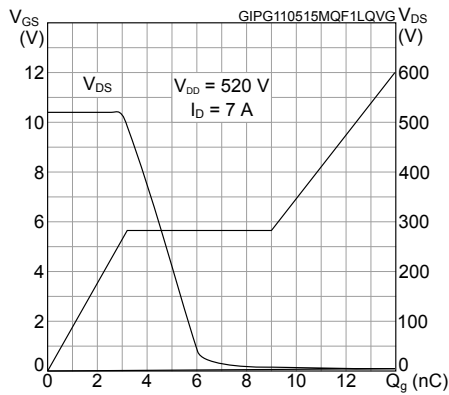
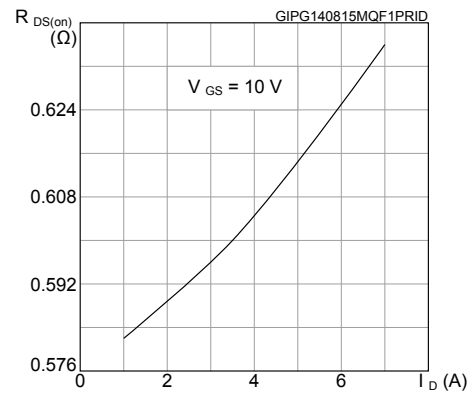
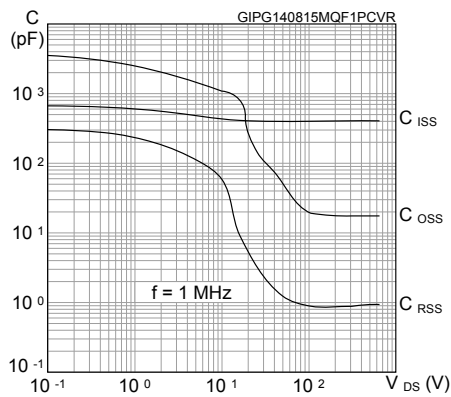
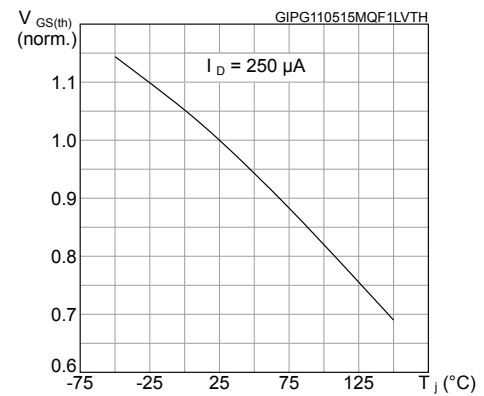
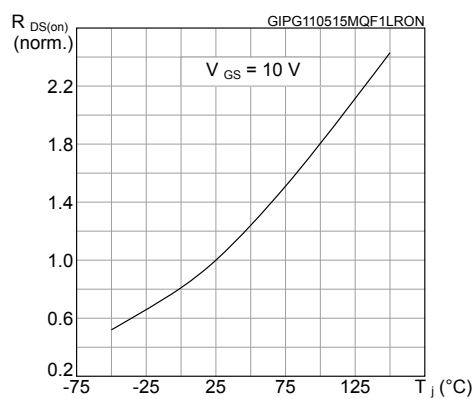
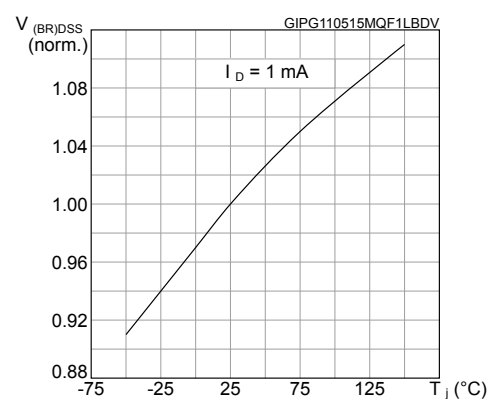
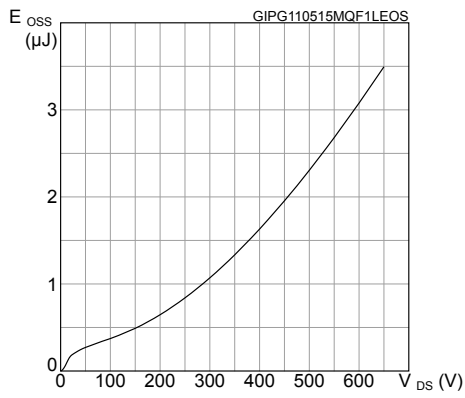
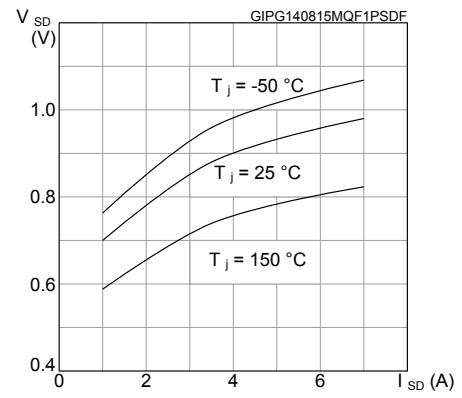
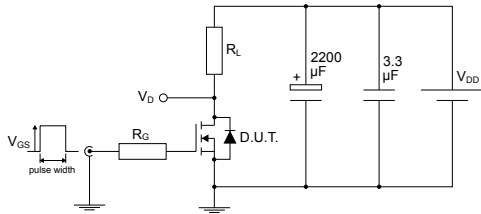
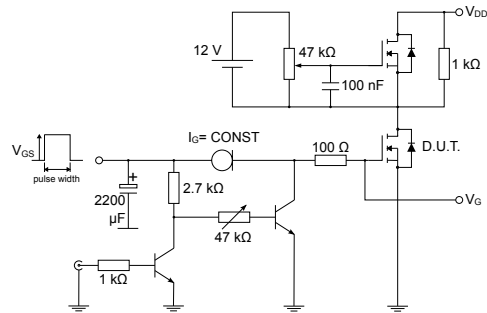
Figure 7. Gate charge vs gate-source voltage

Figure 8. Static drain-source on-resistance

Figure 9. Capacitance variations

Figure 10. Normalized gate threshold voltage vs temperature

Figure 11. Normalized on-resistance vs temperature

Figure 12. Normalized V(BR)DSS vs temperature


Figure 13. Output capacitance stored energy

Figure 14. Source-drain diode forward characteristics


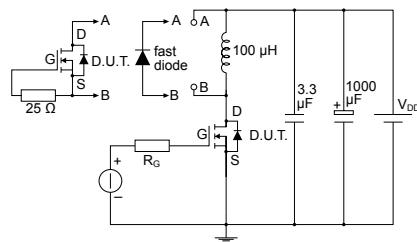
3 Test circuits

Figure 15. Test circuit for resistive load switching times


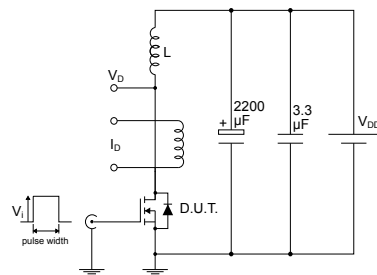
AM01468v1

Figure 16. Test circuit for gate charge behavior


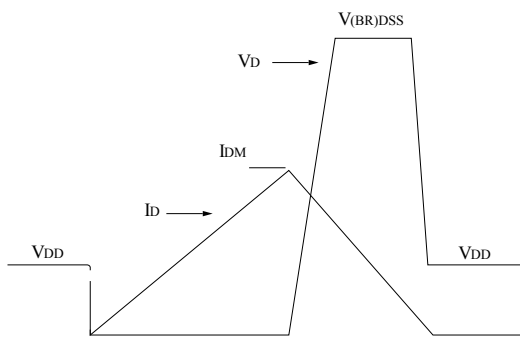
AM01469v1

Figure 17. Test circuit for inductive load switching and diode recovery times


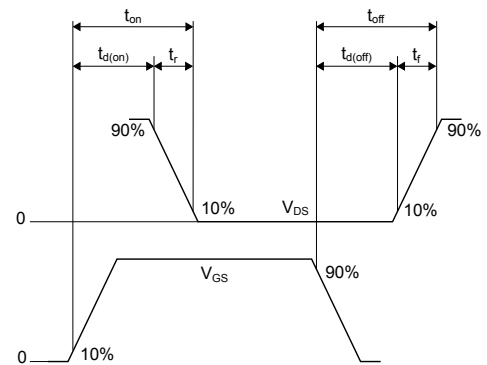
AM01470v1

Figure 18. Unclamped inductive load test circuit


AM01471v1

Figure 19. Unclamped inductive waveform


AM01472v1

Figure 20. Switching time waveform


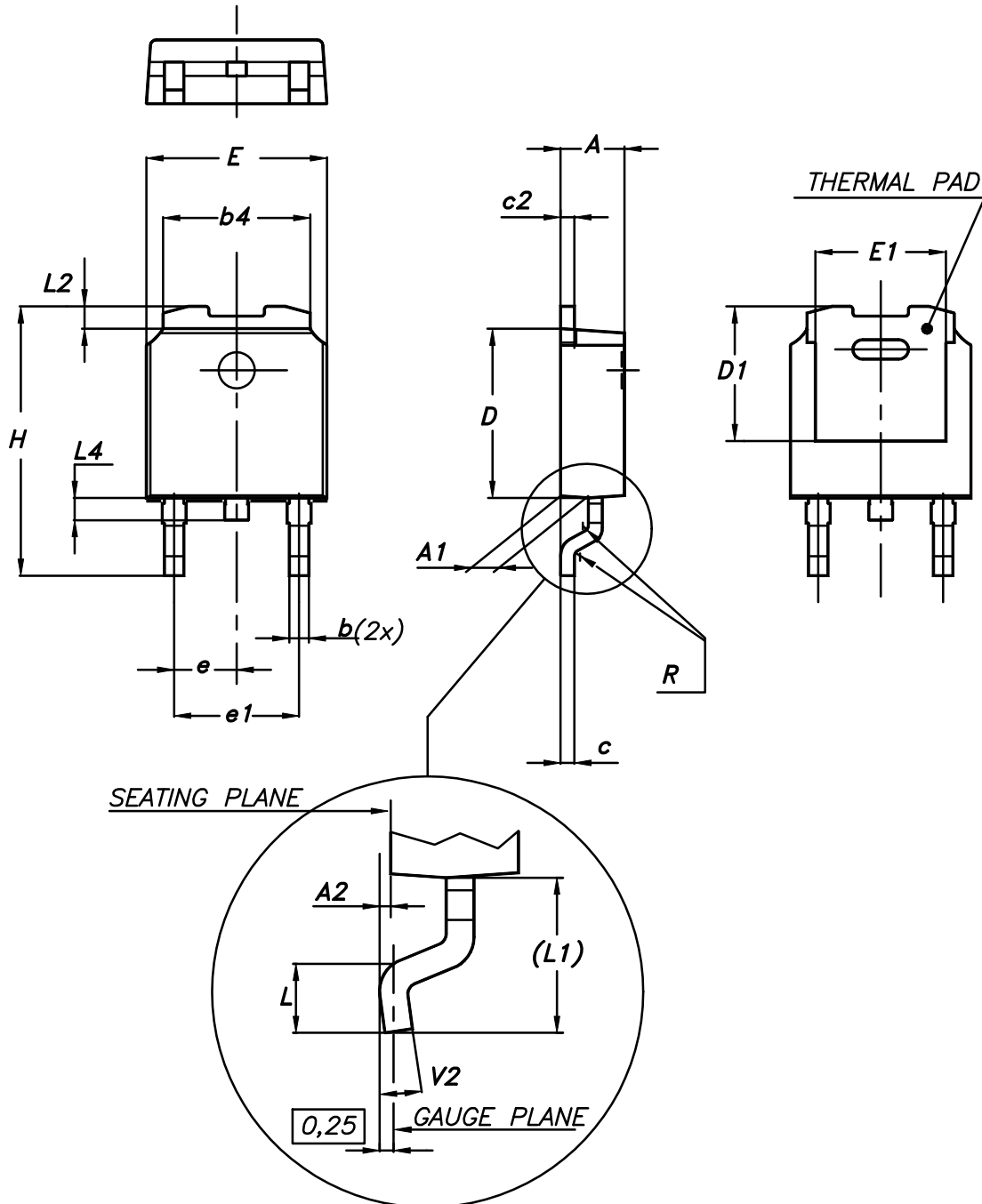
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 21. DPAK (TO-252) type A package outline



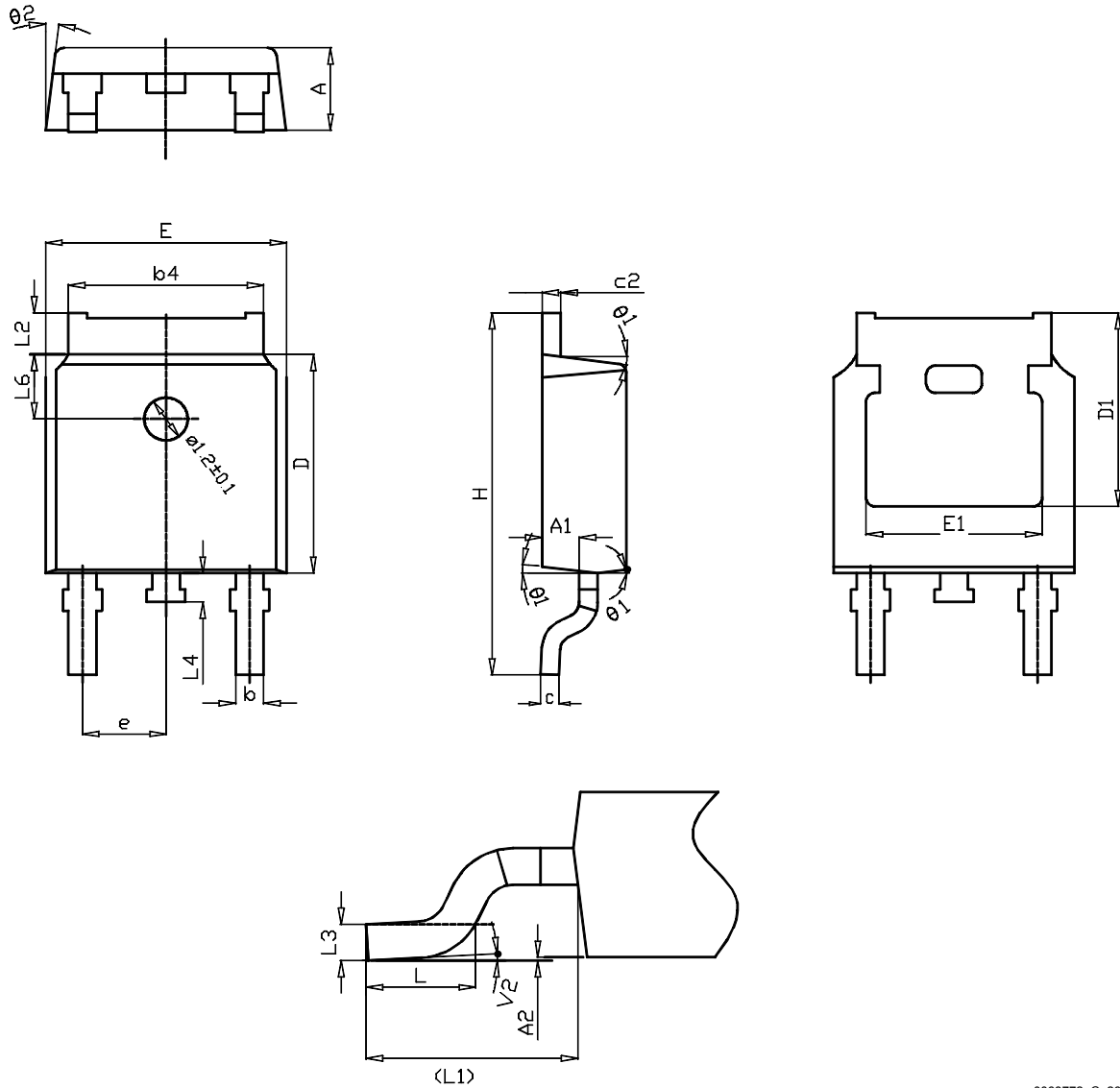
0068772_A_26

Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C package information

Figure 22. DPAK (TO-252) type C package outline



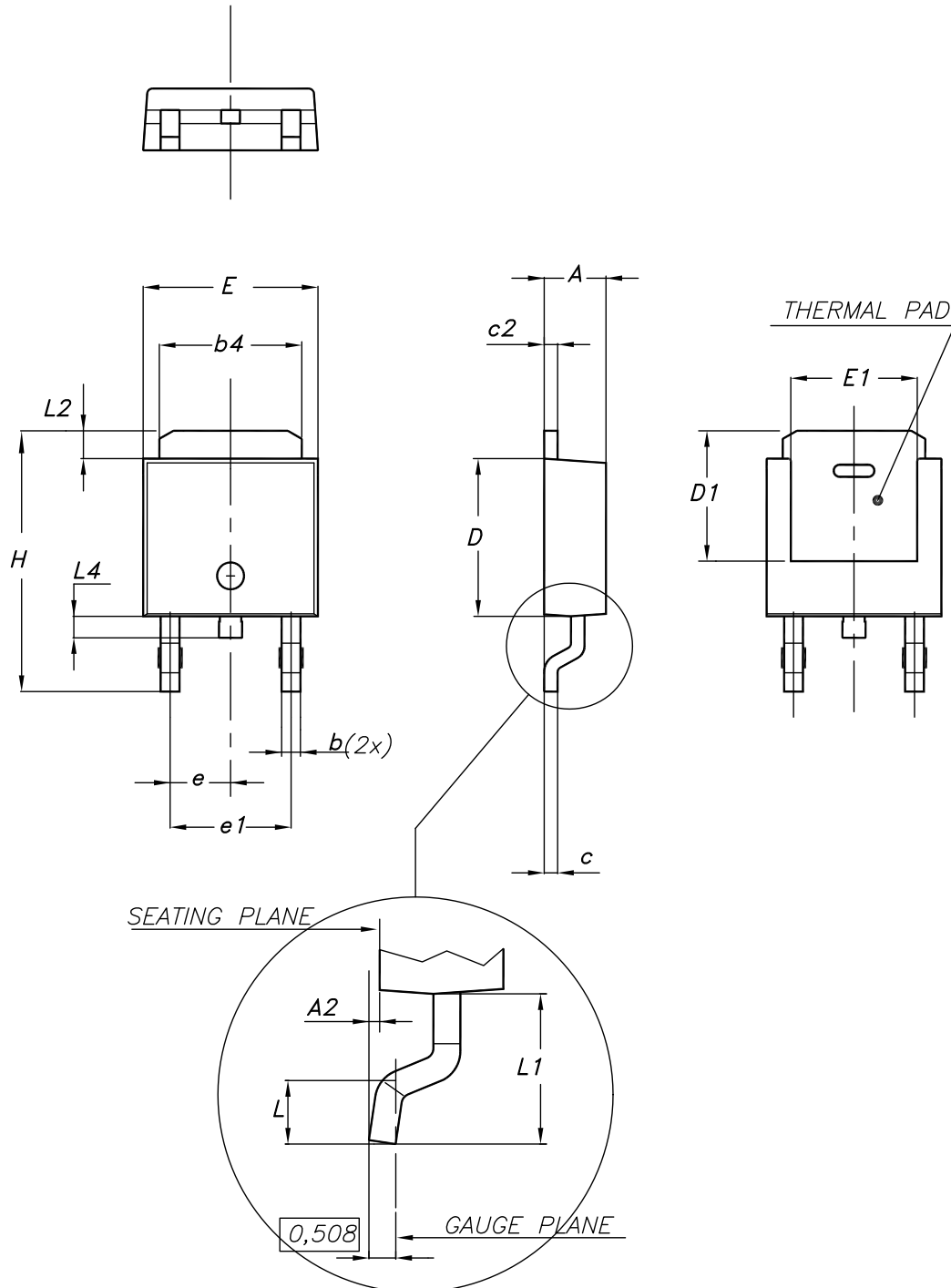
0068772_C_26

Table 9. DPAK (TO-252) type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.3 DPAK (TO-252) type E package information

Figure 23. DPAK (TO-252) type E package outline

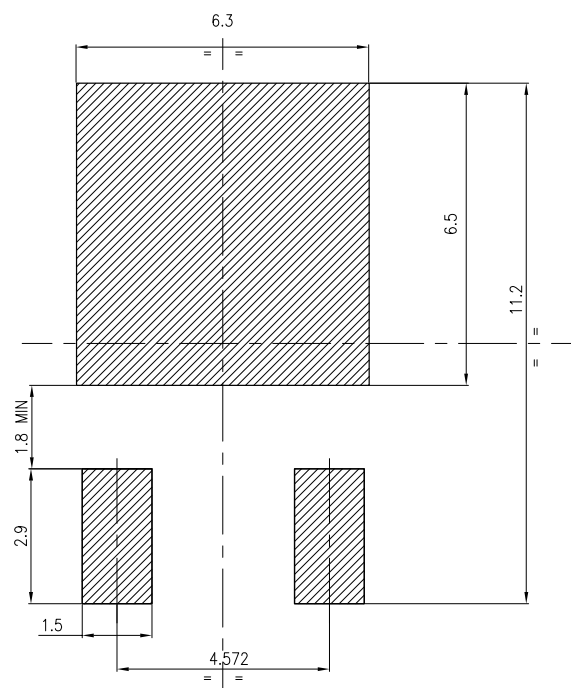


0068772_type-E_rev.26

Table 10. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

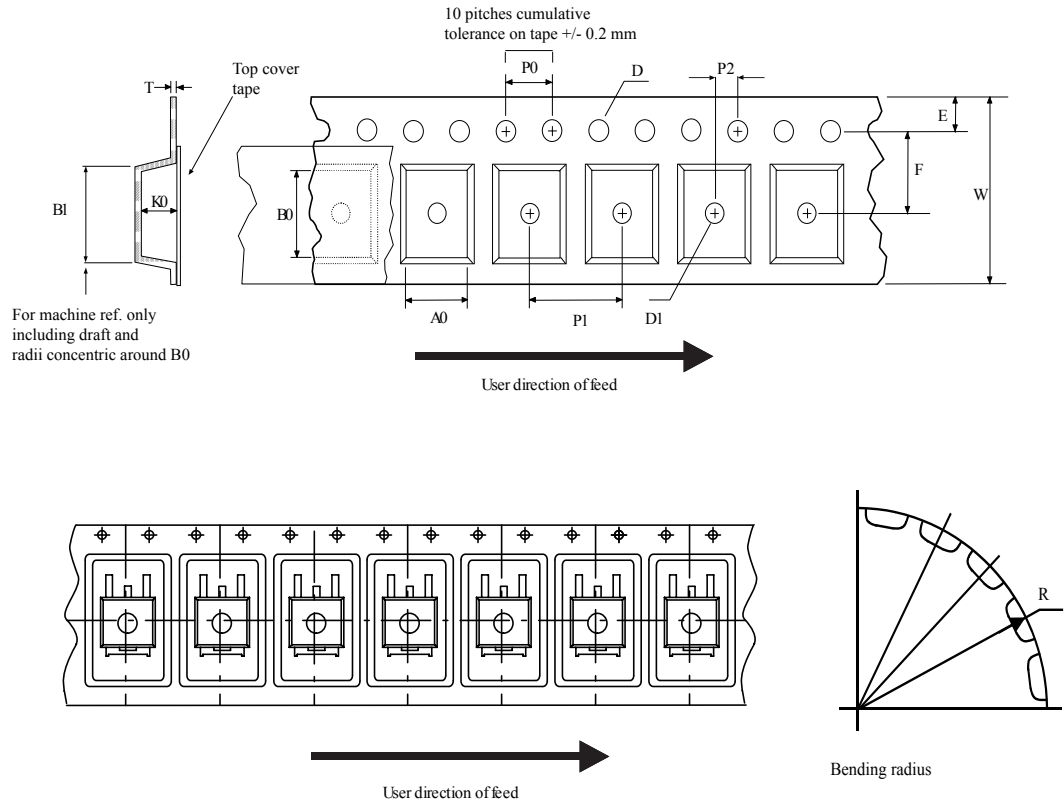
Figure 24. DPAK (TO-252) recommended footprint (dimensions are in mm)



FP_0068772_26

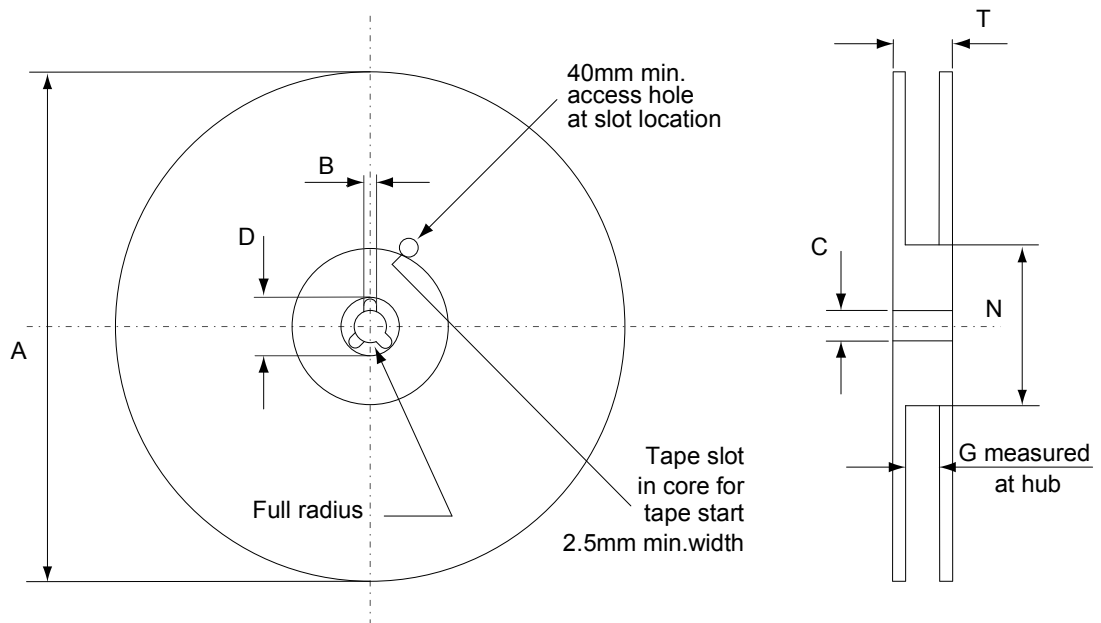
4.4 DPAK (TO-252) packing information

Figure 25. DPAK (TO-252) tape outline



AM08852v1

Figure 26. DPAK (TO-252) reel outline



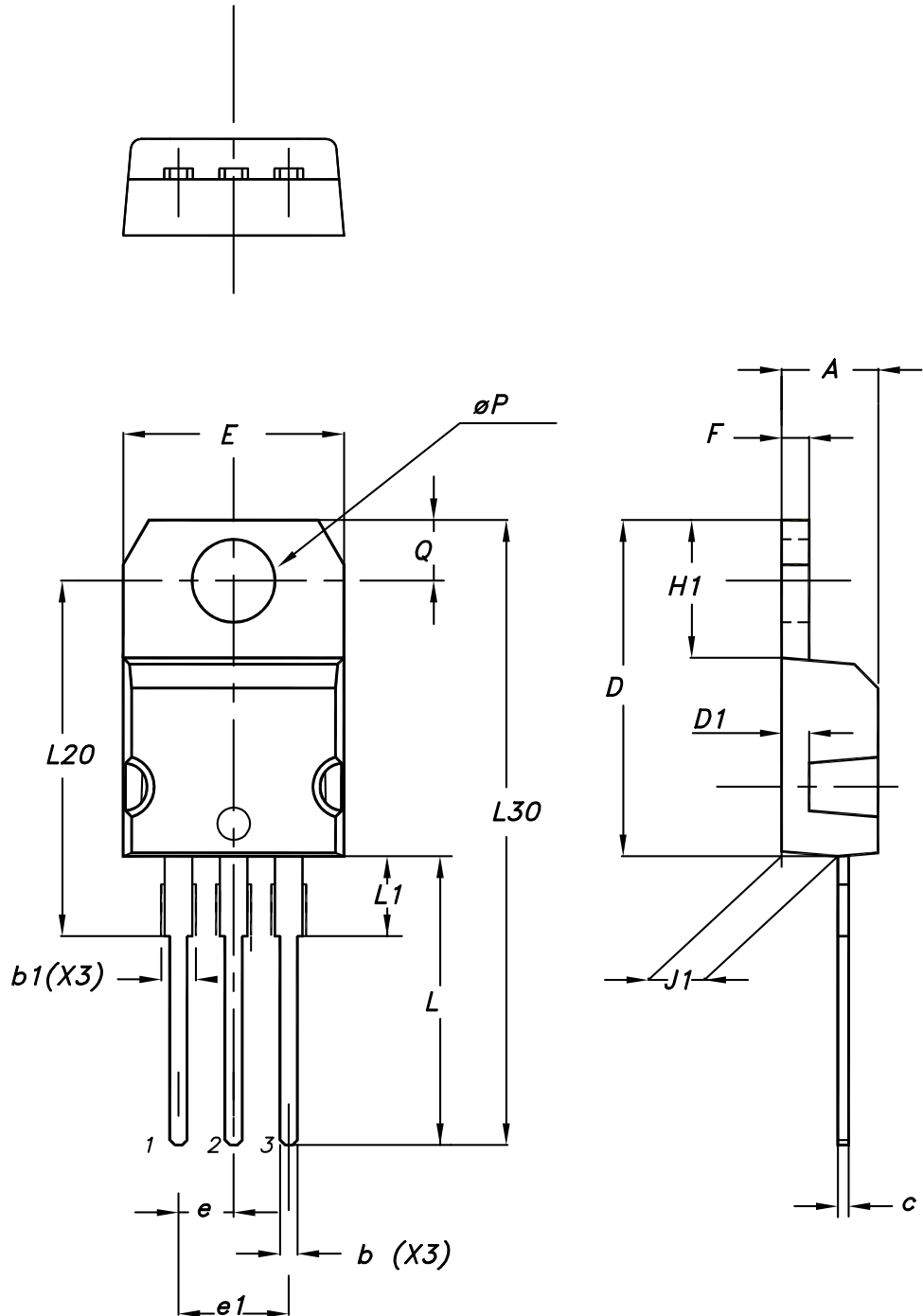
AM06038v1

Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220 type A package information

Figure 27. TO-220 type A package outline



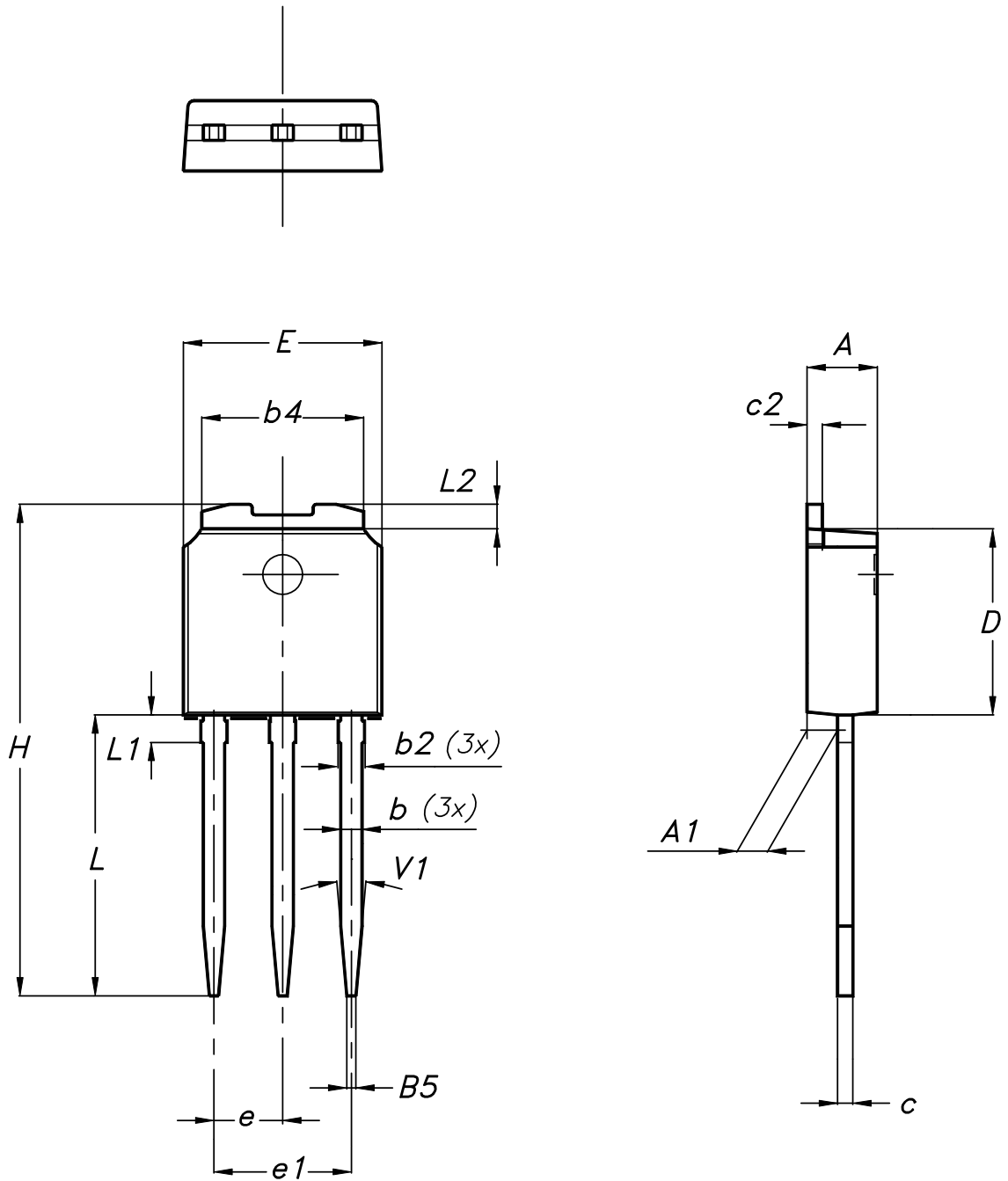
0015988_typeA_Rev_22

Table 12. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.6 IPAK (TO-251) type A package information

Figure 28. IPAK (TO-251) type A package outline



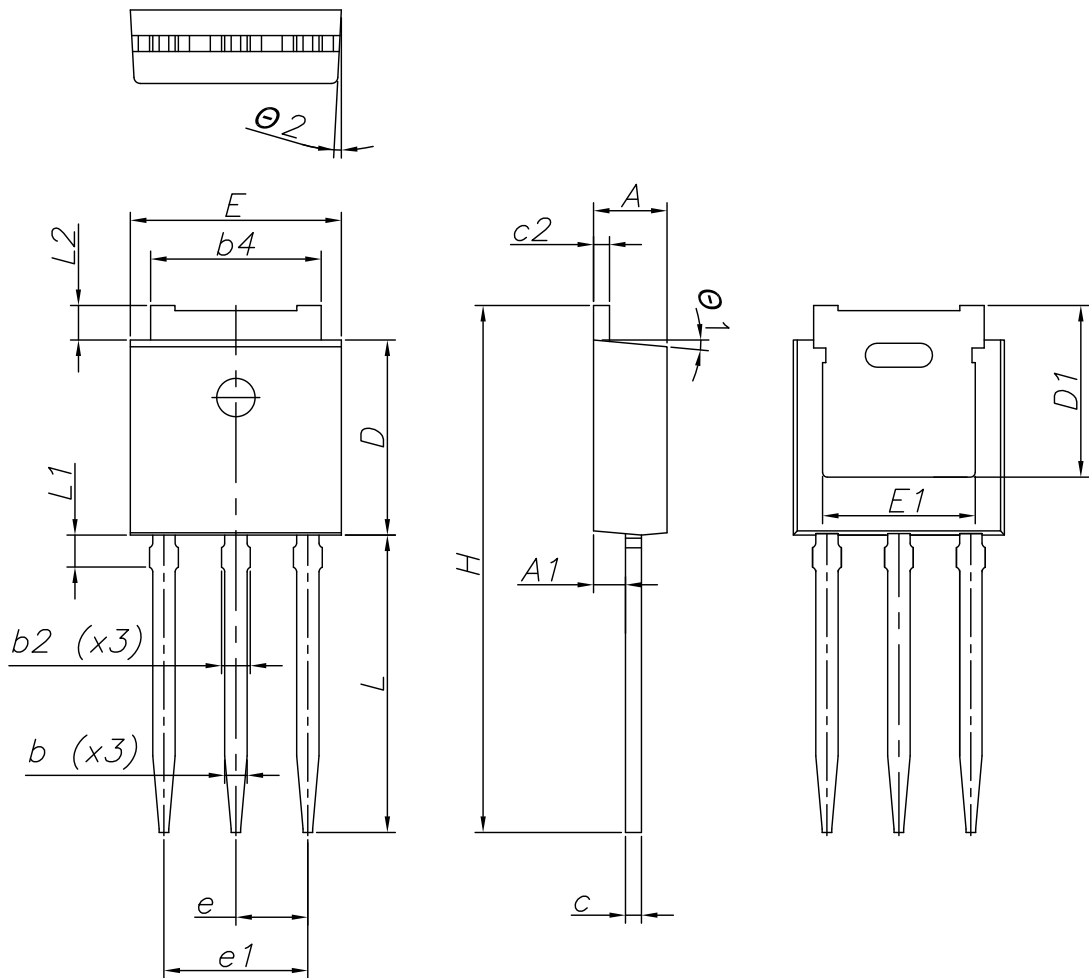
0068771_IK_typeA_rev14

Table 13. IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.7 IPAK (TO-251) type C package information

Figure 29. IPAK (TO-251) type C package outline



0068771_IK_typeC_rev14

Table 14. IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Ordering information

Table 15. Ordering information

Order code	Marking	Package	Packing
STD11N65M2	11N65M2	DPAK	Tape and reel
STP11N65M2		TO-220	Tube
STU11N65M2		IPAK	

Revision history

Table 16. Document revision history

Date	Revision	Changes
16-May-2014	1	First release.
14-Aug-2015	2	Text and formatting changes throughout document. On cover page: - updated <i>Title, Features and Description</i> In section <i>Electrical characteristics</i> : - updated and renamed table <i>Static</i> (was On /off states) Updated section <i>Electrical characteristics (curves)</i> Updated and renamed section <i>Package information</i> (was Package mechanical data)
17-Aug-2015	3	Datasheet promoted from preliminary data to production data. In section <i>Electrical ratings</i> : - updated and renamed table <i>Absolute maximum ratings</i> In section <i>Electrical characteristics</i> : - updated table <i>Source-drain diode</i> In section <i>Electrical characteristics (curves)</i> - updated figure <i>Thermal impedance for DPAK and IPAK</i> Updated and renamed section <i>IPAK (TO-251) Type C package information</i> (was IPAK (TO-251) Type A package information)
07-Sep-2015	4	Minor text and formatting changes throughout document.
16-Oct-2018	5	Updated Section 4 Package information . Minor text changes.
18-Jun-2019	6	Updated Section 3 Minor text changes.

Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical characteristics (curves)	5
3	Test circuits	8
4	Package information	9
4.1	DPAK (TO-252) type A package information	9
4.2	DPAK (TO-252) type C package information	11
4.3	DPAK (TO-252) type E package information	13
4.4	DPAK (TO-252) packing information	15
4.5	TO-220 type A package information	17
4.6	IPAK (TO-251) type A package information	19
4.7	IPAK (TO-251) type C package information	21
5	Ordering information	24
	Revision history	25

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, please refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2019 STMicroelectronics – All rights reserved



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.